

## Small Signal Diodes

Vishay Semiconductor (Austria) Ges.m.b.H.

## QualPack



**PLZ-Series** 

Zener Diodes Permitting 500 mW Power Dissipation Industrial Grade / Part No.: ....G3/H







# PLZ-Series Zener Diodes Permitting 500 mW Power Dissipation



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### 2. General Product Information

Product Name PLZ-Series

**Function** Zener Diodes Permitting 500 mW Power Dissipation

Package DO-219AC (MicroSMF)

### Locations:

Process:  Locations:	Wafer Plant	Assembly Plant	Final Test	Quality Assurance
Vishay Voecklabruck, Austria				Х
Vishay Heilbronn, Germany	Х			Х
Vishay Budapest, Hungary				
Vishay Shanghai, China				
Vishay Tianjin, China		Х	Х	Х
Hangzhou, China	Х			

**Quality Management Vöcklabruck / AUSTRIA** 

QA Small-Signal-Diodes



### 3. Technology Information

#### Features:

- Silicon planar Zener diodes, ultra small
- Low profile surface mount package
- Low leakage current
- Excellent stability
- High temperature soldering: 260 °C/10 s at terminals
- Wave and reflow solderable (reflow as per JPC/JEDEC<sup>®</sup> J-STD 020) (double wave as per IEC 61760-1)
- MSL level 1 (according J-STD-020)
- Lead (Pb)-free termination finish = "e3" = matte tin (Sn)
- Base P/N-G3 RoHS-compliant, commercial grade
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

### 3.1 Process Technology

Process name: Zener
Base material: - material n-Silicon

- thickness (finished) 125 μm

Passivation: - material CVD Layer

Front metallization: - material Al Back metallization: - material Au

### 3.2 Chip Description

Chip name Zener

Chip size 320  $\mu$ m x 320  $\mu$ m

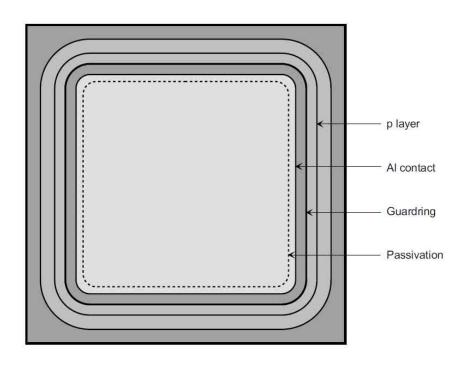


### **Device Cross Sections**

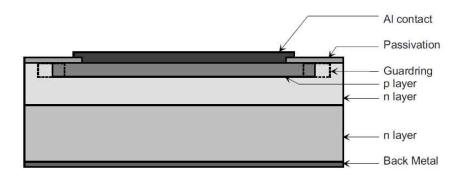
### Zener

(both views are not scaled)

### Top View:



### Sectional View:





### 3.3 Package Technology

Package type:		DO-219AC (MicroSMF)
Package weight:		4,8 mg
Chip separation method:		Sawing
Lead:	- material	Copper
	- lead finish	Sn – matte
	- thickness of plating	≥ 7 µm annealed 1h / 150°C
Die attach:		Eutectic
Package:	- material	Ероху
Marking:	- method	Laser marking
Coding:	- method	Packing label / Barcode
Packing:	- SPEC	IEC 60286 – 3
Tape	- type - material	Carriertape 8mm PC antistatic
Reel	<ul><li>type</li><li>material</li><li>size</li><li>number per</li></ul>	reel PS antistatic 180 mm diameter 4.500 pieces

### Test

Test equipment: TMTT Automated

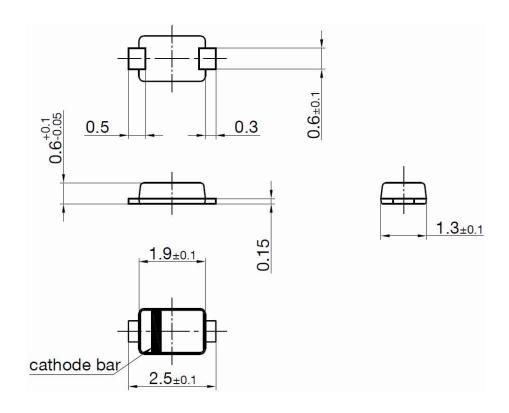
Test temperature  $23 \pm 3^{\circ}\text{C}$ 

Special tests none



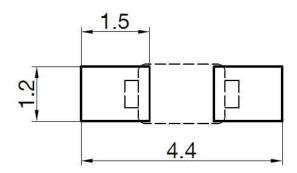
### 3.4 Package Dimensions

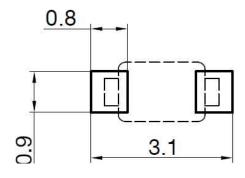
DO-219AC (MicroSMF) Dimension in mm (Inches)



foot print recommendation for wave soldering:

foot print recommendation for reflow soldering:

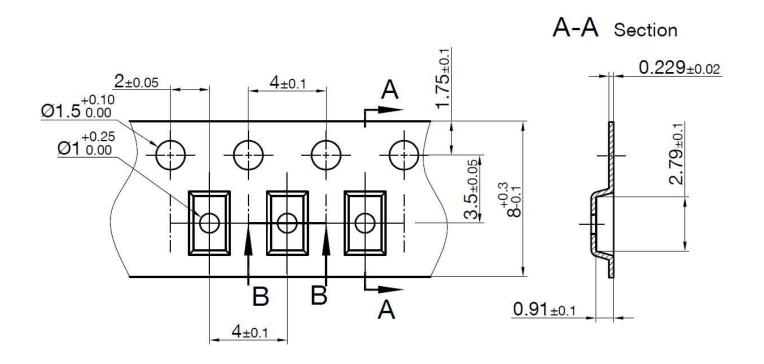




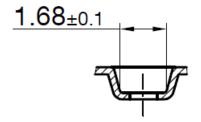


### 3.5 Tape and Reel Dimensions

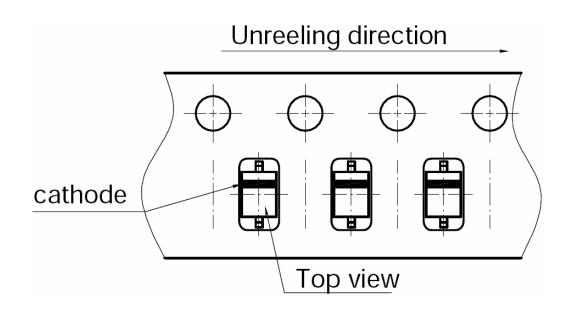
DO-219AC (MicroSMF) (Dimension in mm)

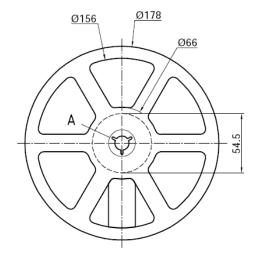


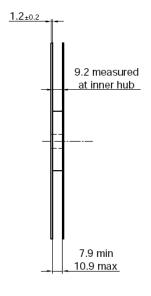
B-B Section

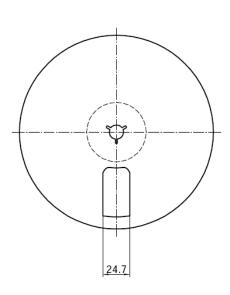




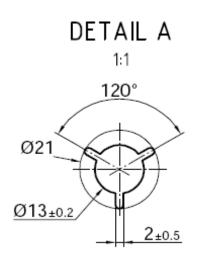


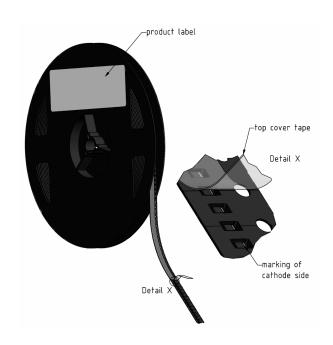








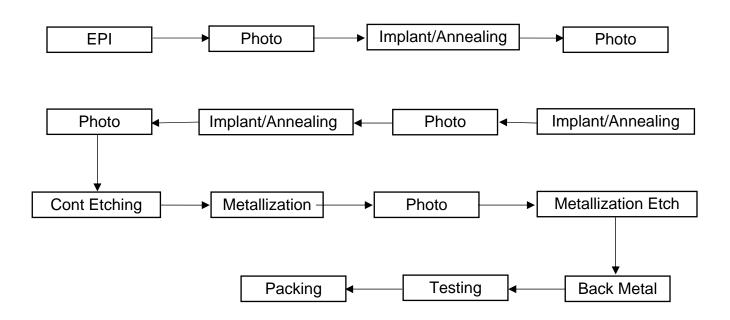






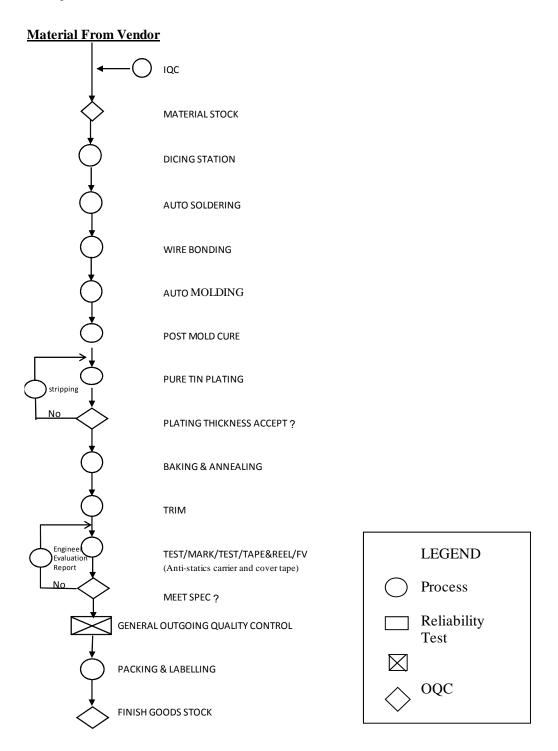
### 3.6 Wafer Process Control

Zener Flow Description



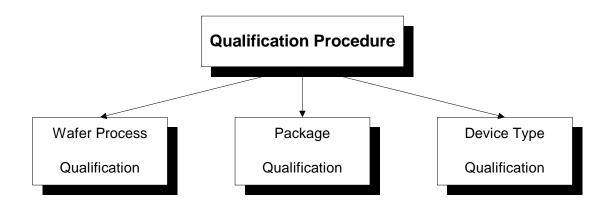


### 3.7 Assembly Process Control





#### 4. Qualification



All product qualifications are split into three distinct areas as shown above. This same procedure is also used to qualify a change. Before a product is released for use it must have been manufactured using a qualified process and package. Before a device is released for production processing it must also have successfully completed its required type specific qualification.

The standard tests which are used for this procedure are shown in the "Qualification Test Plan".

The data shown for the various qualifications may be from structurally similar parts. The wafer process may be qualified using the same process but with a similar package. Similarly the package may be qualified using a similar wafer process.



### 4.1 Change Procedure

Changes are controlled by ECN (Engineering Change Notice). For major changes a customer notification procedure is installed. All customers using affected products have to be notified by PCN (Product Change Notification) at least 60 days prior to the implementation of the change.

A major change is defined as a change which affects the electrical and/or mechanical specification as defined in the data sheet.

Examples of a major change:

- Maximum and minimum data book specifications
- End of Life / Product obsolescence
- Manufacturing location (Site Change)
- Direct raw material
- Lead frame material/design
- Package material/design
- Solder/lead plating process



### 4.2 Reliability Qualification Test Plan

Customer P/N:

ES Spec:

General Specification: JESD47

Supplier: Vishay Semiconductor

Supplier Manufacturing Site

Supplier Generic P/N:

Required PSW Date:

Supplier Internal P/N:

Family Type:

Item	Test	Test Conditions	Exceptions	# Lots	S.S.	Remarks
1	Test	Electrical Characterization @ 25°C.		all	all	
2	Preconditioning	Per JESD22-A113-A Level 1		all	all	
3	External Visual	Per AEC-Q101		all	all	
4	Parametric Verification	Characterization @ -55, 25 & 150°C.		3	25	
5	HTRB	Tj = Tjmax, test @ 0, 500 & 1000 hrs		3	77	
7	Temperature Cycling	Ta = -55 to 150°C., Test @ 0, 500, & 1000 cycles		3	77	
8	Autoclave	96 hrs., Ta = 121°C, rh = 100 % Test @ 0hrs & 96hrs.		3	77	
9	High Humidity High Temp Bias	85C/85RH; Bias @ 80% rated voltage. Test @ 0, 500 & 1000 hrs.		3	77	
10	IOL	Ta = 25°C, Adj for Tj > 100°C; 2 min on/off; Test @ 0, 7500 & 15000 cycles		3	77	
11	ESD	Per AEC-Q101-001 (HBM & MM)		1	30	
12	D.P.A.	Use devices that passed H3TRB & TC		3	2	
13	Physical Dimension	See applicable user device packaging spec.		1	30	
14	Terminal Strength	MIL-STD-750, Method 2036		3	30	
20	Resistance to Solder Heat	Ts = 260°C; Test pre & post		1	30	
21	Solderability	Ts = 245°C Dip & Look Test, Mag = 50X		3	10	
22	Thermal Resistance	JESD-24-3, 24-4, 24-6		1	10	
23	Wire Bond Strength	MIL-STD-750 Method 2037		1	10	
24	Bond Shear	AEC-Q101-003		1	10	
25	Die Shear	MIL-STD-750 Method 2017.2		1	10	
28	Steady State Operation Life	MIL-STD-750 M1038 Cond. B		3	77	
29	High Temp. Storage			3	77	
31	Whisker Test	JESD201, Class 2		3	77	

Comments:		
Prepared by:		
(supplier)		

Pass/fail critera: No catastrophic failures (short/open) (C)

No parameters exeeding spec at and of life (S)

Whisker test pass Class 2



### 4.3 Whisker Test Report

### Whisker Testing Report

JESD201 Class	2
Family	ESMP
Package outline	USMF
P/N	PLZ-20B
Mfg loc	VGSC
Plating line	Meco strip plating line
Plating type	Strip plating
plating solution	Rohm&Haas ST-300T
PB %	<5PPM

Report Date	10/15/13
Finish	Matte
Underlayer	None
Underlayer Spec	N/A
Min thickness Uinch	315.00
Actual thickness	517.61
Min thickness Um	8.00
Actual thickness	13.15
Mitigation	anneal 1H in 150C
DC	/

#### SPEC: MAX allowable Tin whisker length 45um

Total NIC	D		TC -55C/85C 10min	
Lot No.	Precondition	500C	1000C	1500C
1	Pbfree reflow	12.9	18.3	26.1
2	No reflow	21.2	20	23.4
3	Snpb reflow	21.6	23.7	26.6

#### SPEC: MAX allowable Tin whisker length 40um

Lot No.	Precondition	Temp./Humi. 30C/60%RH			
Lot No.	rrecondition	1000H	2000H	3000H	4000H
1	Pbfree reflow	0	0	0	0
2	No reflow	0	0	0	0
3.	Snpb reflow	0	0	0	0

#### SPEC: MAX allowable Tin whisker length 40um

Lot No.	Precondition	High Temp./Humi. 55C/85%RH			
Lot No. Precondition		1000H	2000H	3000H	4000H
1	Pbfree reflow	0	0	26.7	34
2	No reflow	0	0	17.5	23.9
3	Snpb reflow	0	0	26	35.4



### 4.4 ESD Classification

## **ESD - CLASSIFICATION**

		RESULT			
ESD CLASSIFICATON			THSTAND DLTAGE	FAIL/PASS	
НМВ	HUMAN BODY MODEL	>=	8000 V	0/10	
MM	MACHINE MODEL	>=	800 V	0/10	

#### ESD CLASSIFICATION LEVELS:

)Y '100 pF	WITHSTAND VOLTAGE	AEC Q101-001	ESD STM5.1 - 1998	Mil-Std-750D JESD22-A114-A
N BODY Ohm / 10	< 250 V	H0	CLASS 0	CLASS 0
	250 V TO < 500 V	H1A	CLASS 1A	CLASS 1A
HUMAN E	500 V TO < 1000 V	H1B	CLASS 1B	CLASS 1B
l ≥ =	1000 V TO < 2000 V	H1C	CLASS 1C	CLASS 1C
프핌	2000 V TO < 4000 V	H2	CLASS 2	CLASS 2
₽	4000 V TO < 8000 V	H3A	CLASS 3A	CLASS 3A
_	> 8000 V	НЗВ	CLASS 3B	CLASS 3B
MODEL 200 pF	WITHSTAND VOLTAGE	AEC Q101-002	ESD STM5.2 - 2009	JESD22-A115-A
Δô	< 25 V	M0	M1A	A
= MC	25 V TO < 50 V	M1A	M1B	A
ΞÈ	50 V TO < 100 V	M1B	M1C	A
무호	100 V TO < 200 V	M2	M2	A
MACHINE 0 Ohm/2	200 V TO < 400 V	M3	M3	В
	> 400 V	M4	M4	С



### 5. User Information

### 5.1 Reflow Soldering

As per IPC/JEDEC J-STD-020D

total restricted to 3 soldering operations maximum

### Temperature/Time Profile - Infrared-Soldering

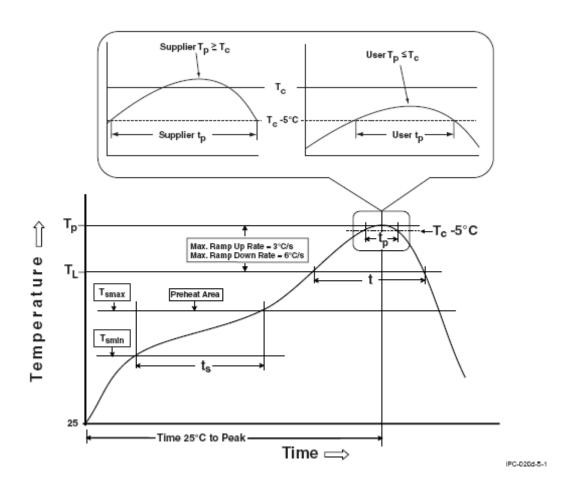




Table 5-2 Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly	
Preheat & Soak			
Temperature min (T <sub>smin</sub> )	100 °C	150 °C	
Temperature max (T <sub>smax</sub> )	150 °C	200 °C	
Time (T <sub>smin</sub> to T <sub>smax</sub> ) (t <sub>s</sub> )	60-120 seconds	60-120 seconds	
Average ramp-up rate (T <sub>smax</sub> to T <sub>p</sub> )	3 °C/second max.	3 °C/second max.	
Liquidous temperature (T <sub>1</sub> )	183 °C	217 °C	
Time at liquidous (t <sub>L</sub> )	60-150 seconds	60-150 seconds	
Peak package body temperature (T <sub>p</sub> )*	See classification temp in Table 4.1	See classification temp in Table 4.2	
Time (t <sub>p</sub> )** within 5 °C of the specified classification temperature (T <sub>c</sub> )	20** seconds	30** seconds	
Average ramp-down rate (T <sub>p</sub> to T <sub>smax</sub> )	6 °C/second max.	6 °C/second max.	
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.	
· · · · · · · · · · · · · · · · · · ·	T \ is defined as a supplier minimum and a s		

- Note 1: All temperatures refer to the center of the package, measured on the package body surface that is facing up during assembly reflow (e.g., live-bug). If parts are reflowed in other than the normal live-bug assembly reflow orientation (i.e., dead-bug), Tp shall be within ± 2 °C of the live-bug Tp and still meet the T<sub>c</sub> requirements, otherwise, the profile shall be adjusted to achieve the latter. To accurately measure actual peak package body temperatures refer to JEP140 for recommended thermocouple use.
- Note 2: Reflow profiles in this document are for classification/preconditioning and are not meant to specify board assembly profiles. Actual board assembly profiles should be developed based on specific process needs and board designs and should not exceed the parameters in Table 5-2.
  - For example, if  $T_c$  is 260 °C and time  $t_p$  is 30 seconds, this means the following for the supplier and the user.
  - For a supplier: The peak temperature must be at least 260 °C. The time above 255 °C must be at least 30 seconds.
  - For a user: The peak temperature must not exceed 260 °C. The time above 255 °C must not exceed 30 seconds.
- Note 3: All components in the test load shall meet the classification profile requirements.
- Note 4: SMD packages classified to a given moisture sensitivity level by using Procedures or Criteria defined within any previous version of J-STD-020, JESD22-A112 (rescinded), IPC-SM-786 (rescinded) do not need to be reclassified to the current revision unless a change in classification level or a higher peak classification temperature is desired.

 $<sup>^*</sup>$  Tolerance for peak profile temperature (T<sub>p</sub>) is defined as a supplier minimum and a user maximum.  $^{**}$  Tolerance for time at peak profile temperature (t<sub>p</sub>) is defined as a supplier minimum and a user maximum.



Table 4-1 SnPb Eutectic Process - Classification Temperatures (Tc)

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm³ ≥350
<2.5 mm	235 ℃	220 °C
≥2.5 mm	220 °C	220 °C

#### Table 4-2 Pb-Free Process - Classification Temperatures (T<sub>c</sub>)

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> 350 - 2000	Volume mm <sup>3</sup> >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm - 2.5 mm	260 °C	250 °C	245 °C
>2.5 mm	250 °C	245 °C	245 °C

- Note 1: At the discretion of the device manufacturer, but not the board assembler/user, the maximum peak package body temperature (T<sub>p</sub>) can exceed the values specified in Tables 4-1 or 4-2. The use of a higher T<sub>p</sub> does not change the classification temperature (T<sub>c</sub>).
- Note 2: Package volume excludes external terminals (e.g., balls, bumps, lands, leads) and/or nonintegral heat sinks.
- Note 3: The maximum component temperature reached during reflow depends on package thickness and volume. The use of convection reflow processes reduces the thermal gradients between packages. However, thermal gradients due to differences in thermal mass of SMD packages may still exist.
- Note 4: Moisture sensitivity levels of components intended for use in a Pb-free assembly process shall be evaluated using the Pb-free classification temperatures and profiles defined in Tables 4.2 and 5-2, whether or not Pb-free.
- Note 5: SMD packages classified to a given moisture sensitivity level by using Procedures or Criteria defined within any previous version of J-STD-020, JESD22-A112 (rescinded), IPC-SM-786 (rescinded) do not need to be reclassified to the current revision unless a change in classification level or a higher peak classification temperature is desired.

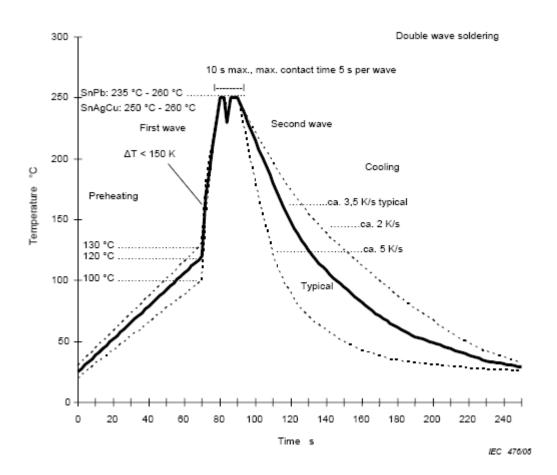


### 5.2 Double Wave Soldering

As per IEC 61760-1

- maximum 2x
- total restricted to 3 soldering operations maximum

### Temperature/Time Profile - Double Wave





#### 6. Environmental Information

### 6.1 Environmental Policy

Vishay Small Signal Products has defined Environmental policy aimed at

- reducing the use of harmful chemicals in its processes
- reducing the content of harmful materials in its products
- using recyclable materials wherever possible
- reducing the energy content of its products

As part of that plan no ozone depleting chemicals are known to be used by either Vishay Small Signal Products or its sub-contractors processes.

All production sites are certified according to the international environmental standard ISO 14001.

### 6.2 Declaration of Material Contents





## **SEMICONDUCTOR Small Signal Products**

#### **MATERIAL CONTENT LIST**

PACKAGE FAMILY: DATE: REVISION:

DO-219AC (MicroSMF)

23-May-2014 2 GREEN (5-2008)\*\*

RoHS COMPLIANT







MATERIAL CONTENT					
Part	Material	CAS N°	Actual weight (mg)	% of weight	ppm of total weigh
Mold	Silica	60676-86-0	1,9934	80,00%	415283
compound	Epoxy Resin	Trade secret	0,2492	10,00%	51910
51,91%	Phenolic resin	Trade secret	0,2367	9,50%	49315
	Carbon Black	1333-86-4	0,0125	0,50%	2596
	TOTAL		2,49		
Lead frame	Cu	7440-50-8	2,045693	94,89%	426186
	Ag	7440-22-4	0,053895	2,50%	11228
44,91%	Fe	7439-89-6	0,050661	2,35%	10554
	Pb	7439-92-1	0,001078	0,05%	225
	Р	7723-14-0	0,001779	0,08%	371
	Zn	7440-66-6	0,002695	0,13%	561
	TOTAL		2,16		
Terminal finish	Sn	7440-31-5	0,11248875	99,99%	23435,156
	other	-	0,00001125	0,01%	2,34375
2,34%	TOTAL		0,11		
Silicon	Si	7440-21-3	0,028	89,5%	5777
chip	Al	7429-90-5	0,001	3,9%	249
	Au	7440-57-5	0,001	4,5%	293
0,65%	0	17778-80-2	0,001	2,2%	140
	TOTAL		0,03		
Bond wire	Cu	7440-50-8	0,0089991	99,99%	1875
	other	-	0,0000009	0,01%	0,188
0,19%	TOTAL		0,01		
Total weight			4,8		

Remarks: Total weight range ± 10%

Reflow Soldering acc. J-STD-020D

\* Not detected

\*\* Please see document "Vishay Green and Halogen-Free Definitions (5-2008)"

http://www.Vishay.com/doc?99902

Material Analysis Reports available on request



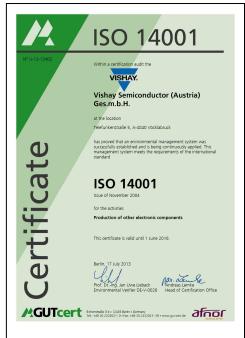
#### Other Data

### 6.3 Approval Certificates

Vishay Semiconductor, Vöcklabruck, Austria ISO/TS16949 / ISO9001 / ISO14001 / OHSAS18001 / EMAS

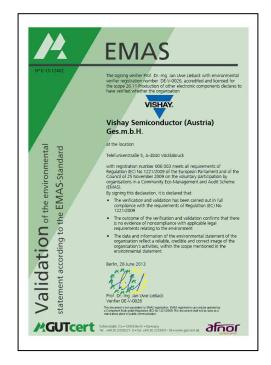






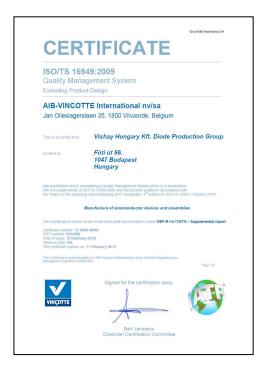








## Vishay Budapest, Hungary ISO/TS16949 / OHSAS18001 (MSZ 28001) / ISO14001









### Vishay, Heilbronn, Germany ISO/TS16949 / ISO9001 / ISO14001









### Vishay Shanghai, China ISO/TS16949 / ISO 9001 / ISO14001 / BS OHSAS 18001











#### 6.4 Databook Reference

The following data references are available for this device:

1. Vishay Databook

2. Applications Notes

Internet homepage: <a href="http://www.vishay.com">http://www.vishay.com</a>

#### **Reference Address**

All enquiries relating to this document should be addressed to the following:

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#### Vishay

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### 7. Locations

General Production Locations of the Division Small Signal Products

Location	Country	City	Assessment
Vishay Vöcklabruck	Austria	Vöcklabruck	ISO/TS 16949 ISO 9001 ISO 14001 OHSAS 18001 EMAS
Vishay Budapest	Hungary	Budapest	ISO/TS 16949 ISO 9001 ISO 14001 OHSAS 18001
Vishay Heilbronn	Germany	Heilbronn	ISO/TS 16949 ISO 9001 ISO 14001
Vishay Shanghai	China	Shanghai	ISO/TS 16949 ISO 9001 ISO 14001
Vishay Tianjin	China	Tianjin	ISO/TS 16949 ISO 9001 ISO 14001
Subcon	China	Chuzhou	ISO/TS 16949 ISO 9001 ISO 14001
Subcon	China	Suzhou	ISO/TS 16949 ISO 9001 ISO 14001 OHSAS 18001
Subcon	Korea	Iksan	ISO/TS 16949 ISO 9001 ISO 14001
Subcon	China	Shanwei	ISO/TS 16949 ISO 9001 ISO 14001
Subcon	China	Chengdu	ISO/TS 16949 ISO 9001 ISO 14001 OHSAS 18001
Wafer Foundry	China	Hangzhou	ISO/TS 16949 ISO 9001 ISO 14001



### 8. Revision history

Issue	Revision	Modification Notice	Applicable from
FEB-14 JUL-14 SEP-14 JUI-15 AUG-15 OCT-15 FEB-16	Revision 1 Revision 2 Revision 3 Revision 4 Revision 5 Revision 6 Revision 7	1 <sup>st</sup> Edition General Update µSMF to MicroSMF MicroSMF to DO-219 (MicroSMF) General Update General Update Industrial Grade	February 2014 July 2014 September 2014 July 2015 August 2015 October 2015 February 2016